Supporting Information

Chemistry of the photoisomerization and thermal reset of nitro-spiropyran and merocyanine molecules on the channel of the MoS2 field effect transistor

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1. The optical contrast method for the flake thickness determination

It is possible to estimate the thickness of the MoS_2 layer by measuring the contrast of the reflected light from the SiO₂ surface with and without the presence of the MoS_2 flake.¹ The contrast is defined with the following equation:

$$C(\lambda) = \frac{R_0(\lambda) - R(\lambda)}{R_0(\lambda)}$$

where $R_0(\lambda)$ and $R(\lambda)$ are the intensities of the reflected light without and with MoS₂ for the wavelength of λ , respectively. It was suggested that the use of λ in the red region is more efficient compare to the use of the blue and green lights.¹ For the device used in this report, the C(λ) of the red light was found to be 0.5, which indicates the number of the layers of the flake to be four from the table calibrated previously.¹

2. Device fabrication process

The substrate (300 nm SiO₂/p⁺⁺Si) was cleaned by acetone and isopropanol separately through ultra-sonication bath for 5 min. Then it was dried by the N₂ gun and then the substrate was treated under UV-O₃ treatment for 30 min to remove any organic impurities. The MoS₂ flakes were transferred to substrate by the mechanically exfoliated technique. The flake was covered by the MMA (methyl methacrylate) and poly (methyl methacrylate) (PMMA A2) resist. Then electron beam lithography (ELS-700, ELIONIX) was carried out for making the electrode pattern. After developing by the developer solvent, Ti (10 nm) /Au (150 nm) source and drain contacts were formed by EB evaporator. Finally, lift-off was done through wet removal by N-methyl-2-pyrrolidone (NMP).



Figure S1. Device fabrication process for MoS₂-FET.

3. Spiropyran coverage estimation on MoS₂ from XPS data

We estimated the coverage as the number of layers of the SP molecule by using the following 6 steps:

Step 1) Calculated he kinetic energy (E_k) of N 1s and Mo 3d electrons.

Step 2) Calculated the mean free path (λ) of N 1s and Mo 3d electrons.

Step 3) Calibrate the pristine MoS_2 thickness, which was 4 layers.

Step 4) Estimate the ratio of areal densities of N and Mo atoms.

Step 5) Examine the signal intensities ratio between N 1s and Mo 3d as the function of the amount of the deposited SP molecule.

Step 6) Determine the thickness of SP layer.

The conversion of the amount of the SP molecule caliculated from the ratio of step 4) is converted into the number of the SP layers based on the model shon in Figure S2, where the lattice o the SP molecule is taken from the data of previously reported STM data of TCNQ on Au surface. The actual XPS spectra, backgroiund subtraction and the calculation with the element coefficients are illustrated in Figure S3.



Figure S2. The model of the surface density ratio of Mo atoms to N atoms. (a) MoS_2 plane as a base was prepared. (b) With reference to the previously reported STM image⁴,

SPs were placed 1.2 nm in the X-axis direction and 0.55 nm in the Y-axis direction. In this model, the benzene ring of the molecule lays parallel to the MoS_2 surface. (c) In the plane of the red frame where the period of MoS_2 and the period of SP are almost the same, we counted the number of N atoms and Mo atoms, respectively. Since there were 24 N atoms and 104 Mo atoms, the areal density ratio of Mo atoms to N atoms was calculated to be ~ 4.3.

Figure S3. The estimation of SP thickness from XPS experiment. (a) The theoretical plot of "SP coverage (layer number)" vs "Intensity ratio of N atom (derived from SP) and Mo atom (derived from MoS_2)". (b) The XPS narrow spectra of N 1s (left) and Mo 3d (right), respectively.

4. Threshold voltage determination

From the I_d - V_g plot we obtain a characteristics I_{ds} which varies linearly with the V_g for a fixed V_d . The I_d - V_g behavior in the linear regime is extrapolated to zero I_d and abscissa we obtain is a good evaluation of the threshold voltage $(V_{th})^5$ shown in Figure S4.

Figure S4. Threshold voltage determination method for the pristine device.

5. Table for the rate constants with corresponding temperatures

The results of the fitting for the plots shown in Figure 4.

Rate Constants (k)	lnk	Temperature, T(K)	1/T
 0.00069	-7.289	298.15	0.00335
0.00505	-5.289	313.15	0.00319
0.00879	-4.734	323.15	0.00309
0.02163	-3.833	333.15	0.00300
0.09066	-2.400	343.15	0.00291
0.22543	-1.489	353.15	0.00283

Table 1. Rate constants with corresponding temperatures.

6. Raman spectroscopy analysis

Figure S5. Raman peaks of pristine MoS_2 , after SP covered, after UV irradiation on SP surface and after heat treatment on MC.

Figure S5 shows the two characteristics peaks E_{2g} and A_{1g} of MoS₂. After SP deposition, E_{2g} and A_{1g} peaks shifted to the left side indicates the n-doping of MoS₂ by SP molecules. After UV irradiation on SP covered surface, both peaks shifted more left side which tells that MC also acting as n dopants for the MoS₂. To recover the former SP molecules device was heated at around 80° C for 3 min thus makes the MC to SP again. This thermal conversion of MC to SP is visible in the Raman spectrum in which the E_{2g} and A_{1g} peaks come back the SP position.

7. Time of Flight Secondary Ionization Mass Spectroscopy Analysis

To further confirm the adsorption configuration of SP, the time-of-flight secondary ionization mass spectroscopy (SIMS) was measured. Figure S6a and b represent the elemental mapping image showing the presence of Mo^+ and $C_{19}H_{19}N_2O_2^+$ ions, respectively. The amplitude of the color scale corresponds to the maximum number of counts. TOF-SIMS confirms the presence of SP over the MoS₂ surface as a $[M + H]^+$ at 323.36 m/z, as shown in Figure S6c.

Figure S6. (a),(b) TOF-SIMS elemental mapping of Mo^+ and $C_{19}H_{19}N_2O_2^+$, respectively; (c) TOF-SIMS spectrum showing the $C_{19}H_{19}N_2O_2^+$ peak as [M+H]

8 Optimized adsorption configurations of Spiropyran and Merocyanine on MoS₂

The optimized adsorption configuration for SP and MC molecules after the structural optimization starting from various initial configurations, which are plausible for the adsorption. Thus, they are representing the local minimum structures. For the SP molecule, two large group are considered; group A is the two apex of the bent configuration of SP are both attached to the substrate, and group B is that one of the two perimeters of the V shape molecule is adsorbed on the substrate in a flat-lying manner. For MC, the tilted-configuration of basically flat molecule structures is calculated to have the most stable configuration. Severn models for each (total 21 models) were calculated and shown in Figure S7.

In addition, the calculated total energies for the models are shown in Table S2. We see the SP molecules give stable configurations than the MC molecules. The most stable model is SP-MoS2-B3 which is shown in the main text.

SP_MoS2_A_3

SP_MoS2_A_4

SP_MoS2_A_7

SP_MoS2_B_1

SP_MoS2_B_2

SP_MoS2_B_3

11

SP_MoS2_B_6

SP_MoS2_B_5

SP_MoS2_B_4

MC_MoS2_2

SP_MoS2_B_7

Figure S7. Optimized structures of the SP and MC molecules adsorbed on MoS_2 surface. The calculation was started from various plausible configurations and the results of the structural optimization by VASP for the local minimum are illustrated.

Table S2. The total energies of the models of Figure S7. The most stable configuration is SP-MoS2-B3 which is shown with a bold font. For the MC molecule, the model of MC_MoS2_6 gives the lowest energy.

	Total energy (eV)
MC_MoS2_1	-3535.539
MC_MoS2_2	-3535.5134
MC_MoS2_3	-3535.5354
MC_MoS2_4	-3535.4873
MC_MoS2_5	-3535.5161
MC_MoS2_6	-3535.5711
MC_MoS2_7	-3535.4923
SP_MoS2_A_1	-3535.5693
SP_MoS2_A_2	-3535.5264
SP_MoS2_A_3	-3535.5441
SP_MoS2_A_4	-3535.5702
SP_MoS2_A_5	-3535.5171
SP_MoS2_A_6	-3535.5493
SP_MoS2_A_7	-3535.5674
SP_MoS2_B_1	-3535.4933
SP_MoS2_B_2	-3535.5386
SP_MoS2_B_3	-3535.6159
SP_MoS2_B_4	-3535.5654
SP_MoS2_B_5	-3535.4291
SP_MoS2_B_6	-3535.5037

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